CLAIMS

ī	1. A wave-snaped capacitor, formed over a base conductive layer, said base
2	conductive layer over a base insulator layer on a die, the capacitor including:
3	a wave-shaped pattern in the base conductive layer comprising at least two
4	adjacent trenches in the base conductive layer;
5	a multilayer structure contoured over the base conductive layer, the multilayer
6	structure comprising:
7	a first plate layer in electrical contact with the base conductive layer;
8	an insulating layer over the first plate layer;
9	a second plate layer over the insulating layer; and
10	a interconnect layer over the multilayer structure, including at least one
11	interconnection with the second plate layer.
1	2. The device of claim 1, wherein the at least two adjacent trenches are formed
2	by a lithographic or direct writing process and the multilayer structure has a thickness
3	along the sidewalls of the trench that is less than half of a minimum feature size of the
4	lithographic or direct writing process.
	2. The device of claim 1 subgrain the base conductive lover and the first
1	3. The device of claim 1, wherein the base conductive layer and the first
2	conductive layer are the same structure.
1	4. The device of claim 3, wherein the at least two adjacent trenches are formed

by a lithographic process and the multilayer structure has a thickness along the

sidewalls of the trench that is less than half of a minimum feature size of the

lithographic or direct writing process.

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